

シリコンカーバイドウエハー (SiC Wafer)
2 インチ 半絶縁型 4H-SiC ウエハー



SUBSTRATE PROPERTY	Production Grade	Research Grade	Dummy Grade
Diameter	50.8 mm ± 0.38 mm		
Surface Orientation	{ 0001} ± 0.2°		
Primary Flat Orientation	<11-20> ± 5.0°		
Secondary Flat Orientation	90.0° CW from Primary ± 5.0°, silicon face up		
Primary Flat Length	16.0 mm ± 1.65 mm		
Secondary Flat Length	8.0 mm ± 1.65 mm		
Wafer Edge	Chamfer		
Micropipe Density	≤5 micropipes/ cm ²	≤10 micropipes/ cm ²	≤50 micropipes/ cm ²
Resistivity	≥1E5 Ω·cm		(area 75%) ≥1E5 Ω·cm
Thickness	350.0 μm ± 25.0 μm		350.0 μm ± 50.0 μm
TTV	≤10 μm		≤15 μm
Bow (absolute value)	≤10 μm		≤15 μm
Warp	≤35 μm		≤45μm
Surface Finish	Double Side Polish, Si Face CMP (chemical polishing)		
Surface Roughness	CMP Si Face Ra≤0.5 nm		N/A
Cracks by high -intensity light	None permitted		
Edge chips/indents by diffuse lighting	None permitted	Qty.2 < 1.0 mm width and depth	Qty.2 < 1.0 mm width and depth
Total usable area	≥90%	≥80%	N/A

*The other specifications can be customized according to customer's requirements



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シリコンカーバイドウエハー (SiC Wafer)
3 インチ 半絶縁型 4H-SiC ウエハー



SUBSTRATE PROPERTY	Production Grade	Research Grade	Dummy Grade
Diameter	76.2 mm ± 0.38 mm		
Surface Orientation	{0001} ± 0.2°		
Primary Flat Orientation	<11-20> ± 5.0°		
Secondary Flat Orientation	90.0° CW from Primary ± 5.0°, silicon face up		
Primary Flat Length	22.0 mm ± 2.0 mm		
Secondary Flat Length	11.0 mm ± 1.5mm		
Wafer Edge	Chamfer		
Micropipe Density	≤5 micropipes/ cm ²	≤10 micropipes/ cm ²	≤50 micropipes/ cm ²
Resistivity	≥1E5 Ω·cm		(area 75%) ≥1E5 Ω·cm
Thickness	350.0 μm ± 25.0 μm		350.0 μm ± 50.0 μm
TTV	≤10 μm		≤15 μm
Bow (absolute value)	≤15 μm		≤25 μm
Warp	≤35 μm		≤45 μm
Surface Finish	Double Side Polish, Si Face CMP (chemical polishing)		
Surface Roughness	CMP Si Face Ra≤0.5 nm		N/A
Cracks by high -intensity light	None permitted		
Edge chips/indents by diffuse lighting	None permitted	Qty.2 < 1.0 mm width and depth	Qty.2 < 1.0 mm width and depth
Total usable area	>90%	>80%	N/A

*The other specifications can be customized according to customer's requirements



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シリコンカーバイドウエハー (SiC Wafer)
4 インチ 半絶縁型 4H-SiC ウエハー



SUBSTRATE PROPERTY	Production Grade	Research Grade	Dummy Grade
Diameter	100.0 mm + 0.0/-0.5 mm		
Surface Orientation	{0001} ± 0.2°		
Primary Fl at Orientation	<11-20> ± 5.0°		
Secondary Flat Orientation	90.0° CW from Primary ± 5.0°, silicon face up		
Primary Flat Length	32.5 mm ± 2.0 mm		
Secondary Flat Length	18.0 mm ± 2.0 mm		
Wafer Edge	Chamfer		
Micropipe Density	≤5 micropipes/ cm ²	≤10 micropipes/ cm ²	≤50 micropipes/ cm ²
Resistivity	≥1E5 Ω-cm		(area 75%) ≥1E5 Ω-cm
Thickness	350.0 μm ± 25.0 μm or 500.0 μm ± 25.0 μm		500.0 μm ± 50.0 μm or 350.0 μm ± 50.0 μm
TTV	≤10μm		≤15 μm
Bow (absolute value)	≤25 μm		≤30 μm
Warp	≤45 μm		≤60 μm
Surface Finish	Double Side Polish, Si Face CMP (chemical polishing)		
Surface Roughness	CMP Si Face Ra≤0.5 nm		N/A
Cracks by high -intensity light	None permitted		
Edge chips/indents by diffuse lighting	None permitted	Qty.2 < 1.0 mm width and depth	Qty.2 < 1.0 mm width and depth
Total usable area	≥90%	≥80%	N/A

*The other specifications can be customized according to customer 's requirements



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